

May 2010

# FDI8441\_F085

# N-Channel PowerTrench® MOSFET 40V, 80A, 2.7m $\Omega$

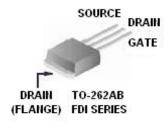
#### **Features**

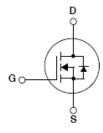
- Typ  $r_{DS(on)}$  = 2.2m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 80A
- Typ  $Q_{g(10)}$  = 215nC at  $V_{GS}$  = 10V
- Low Miller Charge
- Low Q<sub>rr</sub> Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

# **Applications**

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter / Alternator
- Distributed Power Architectures and VRMs
- Primary Switch for 12V Systems







# $\textbf{MOSFET Maximum Ratings} \ \, \text{$T_C$ = $25^{\circ}$C unless otherwise noted}$

Symbol	Parameter	Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage		40	V
$V_{GS}$	Gate to Source Voltage	±20	V	
	Drain Current Continuous (T <sub>C</sub> < 160°C, V <sub>GS</sub> = 10V)		80	
I <sub>D</sub>	Continuous ( $T_{amb} = 25^{\circ}C$ , $V_{GS} = 10V$ , with $R_{\theta JA} = 43^{\circ}C/W$ )		26	Α
	Pulsed		See Figure 4	
E <sub>AS</sub>	Single Pulse Avalanche Energy (	Note 1)	947	mJ
Б	Power dissipation		300	W
$P_{D}$	Derate above 25°C		2	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature		-55 to 175	°C

### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance Junction to Case		0.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	(Note 2)	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in <sup>2</sup> copper pad area		43	°C/W

# **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDI8441	FDI8441_F085	TO-262AB	Tube	NA	50 units

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units

#### **Off Characteristics**

B <sub>VDSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \text{mA}, V_{GS} = 0 \text{V}$		40	1	-	V
	Zero Gate Voltage Drain Current	$V_{DS} = 32V$		-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{GS} = 0V$	$T_J = 150$ °C	-	1	250	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>GS</sub> = ±20V		-	-	±100	nA

#### **On Characteristics**

$V_{GS}$	S(th)	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.8	4	V
			I <sub>D</sub> = 80A, V <sub>GS</sub> = 10V	-	2.2	2.7	
r <sub>DS(</sub>	(on)	Drain to Source On Resistance	I <sub>D</sub> = 80A, V <sub>GS</sub> = 10V, T <sub>J</sub> = 175°C	-	3.8	4.7	mΩ

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 25V V	-V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, -f = 1MHz		15000	-	pF
Coss	Output Capacitance				1250	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 11/11/12			685	-	pF
$R_G$	Gate Resistance	$V_{GS} = 0.5V, f = 1$	V <sub>GS</sub> = 0.5V, f = 1MHz		1.1	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V		-	215	280	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to $2V$	V <sub>DD</sub> = 20V	-	29	38	nC
$Q_{gs}$	Gate to Source Gate Charge	$I_D = 35A$		-	60	-	nC
Q <sub>gs2</sub>	Gate Charge Threshold to Plateau	$I_g = 1mA$		-	32	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	49	-	nC

# Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
<u> </u>						

#### **Switching Characteristics**

t <sub>(on)</sub>	Turn-On Time		-	-	77	ns
t <sub>d(on)</sub>	Turn-On Delay Time		-	23	-	ns
t <sub>r</sub>	Turn-On Rise Time	V <sub>DD</sub> = 20V, I <sub>D</sub> = 35A	-	24	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10V, R_{GS} = 1.5\Omega$		75	-	ns
t <sub>f</sub>	Turn-Off Fall Time		-	17.9	-	ns
t <sub>off</sub>	Turn-Off Time		-	-	147	ns

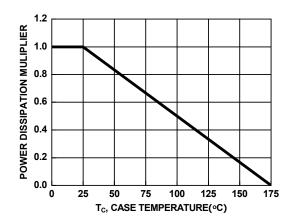
#### **Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Voltage	I <sub>SD</sub> = 35A	-	0.8	1.25	V
		I <sub>SD</sub> = 15A	-	0.8	1.0	٧
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 35A$ , di/dt = $100A/\mu s$	-	52	68	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$I_F = 35A$ , di/dt = 100A/ $\mu$ s	-	76	99	nC

Notes: 1: Starting T<sub>J</sub> = 25°C, L = 0.46mH, I<sub>AS</sub> = 64A. 2: Pulse width = 100s.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/
All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

# **Typical Characteristics**



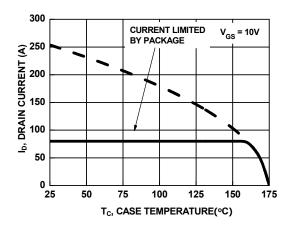


Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs Case Temperature

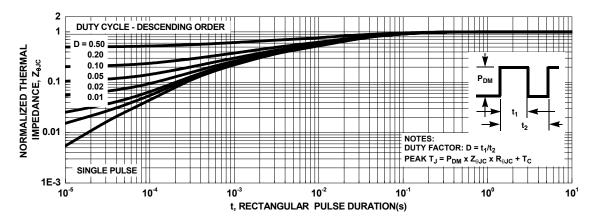


Figure 3. Normalized Maximum Transient Thermal Impedance

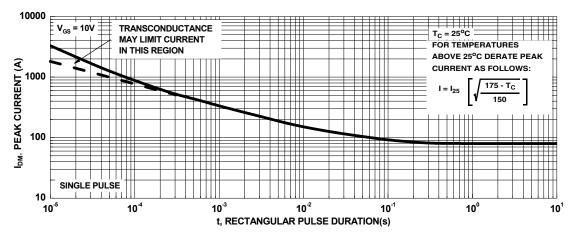


Figure 4. Peak Current Capability

# **Typical Characteristics**

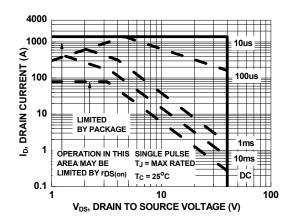
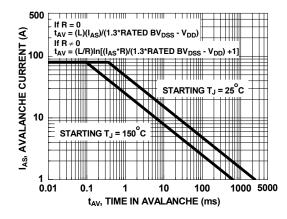


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

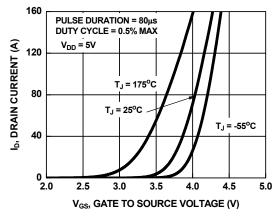


Figure 7. Transfer Characteristics

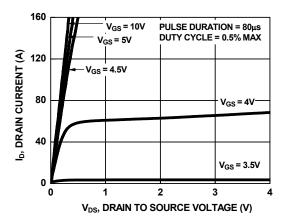


Figure 8. Saturation Characteristics

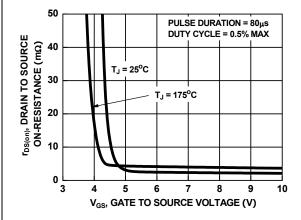


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

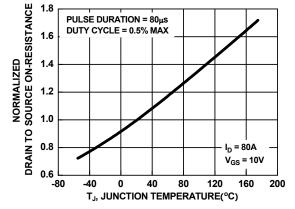


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

# **Typical Characteristics**

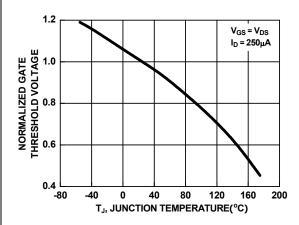


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

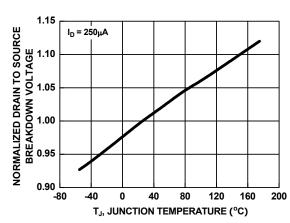


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

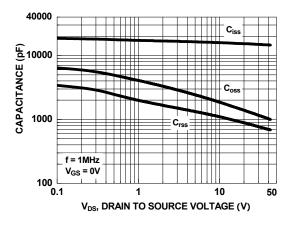


Figure 13. Capacitance vs Drain to Source Voltage

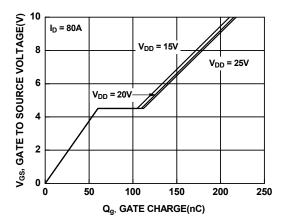


Figure 14. Gate Charge vs Gate to Source Voltage



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